

NIT-Epitem GaN FET Project

Reactor: Veeco D-125 (3x2" substrates)

Substrate: 2" sapphire (0.15° off) or your spec.

Structure : standard or full ordered

Attached data : XRD (Philips X'Pert MRD)

Rs map (LEI 1510B)

mobility (non-destructive measurements, LEI 1600)

Epitem, a new venture established in collaboration between NIT (Nippon Institute of Technology) and Professor Suzuki at NIT, can provide you GaN FET epi wafers.

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